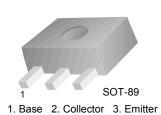
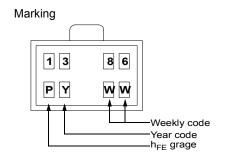


# FJC1386 PNP Epitaxial Silicon Transistor

## **Low Saturation Transistor Medium Power Amplifier**

- Complement to FJC2098
- · High Collector Current
- · Low Collector-Emitter Saturation Voltage





## Absolute Maximum Ratings T<sub>a</sub> = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub> Collector-Base Voltage		-30	V
V <sub>CEO</sub> Collector-Emitter Voltage		-20	V
V <sub>EBO</sub>	Emitter-Base Voltage	-6	V
I <sub>C</sub>	Collector Current (DC)	-5	A
P <sub>C</sub>	Power Dissipation (T <sub>a</sub> = 25°C)	0.5	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 to +150	°C

#### Electrical Characteristics T<sub>a</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C = -50\mu A, I_E = 0$	-30		V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	$I_{C} = -1 \text{mA}, I_{B} = 0$	-20		V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = -50\mu A, I_C = 0$	-6		V
I <sub>CBO</sub>	Collector-Cutoff Current	$V_{CB} = -20V, V_{B} = 0$		-0.5	μΑ
I <sub>EBO</sub>	Emitter-Cutoff Current	$V_{EB} = -5V, I_{C} = 0$		-0.5	μΑ
h <sub>FE</sub>	DC Current Gain	$V_{CE} = -2V, I_{C} = -0.5A$	80	390	
V <sub>CE (sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -4A, I <sub>B</sub> = -0.1A		-1.0	V
V <sub>BE (sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = -4A, I <sub>B</sub> = -0.1A		-1.5	V

## Thermal Characteristics T<sub>a</sub> = 25°C unless otherwise noted

Symbol	Parameter	Max.	Units
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	250	°C/W

## h<sub>FE</sub> Classification

Classification	Р	Q	R
hFE	80 ~ 180	120 ~ 270	180 ~ 390

## **Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
1386	FJC1386	SOT-89	13"		4,000

### **Typical Performance Characteristics**

Figure 1. Static Characteristic

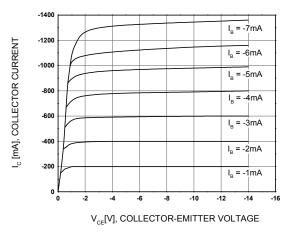
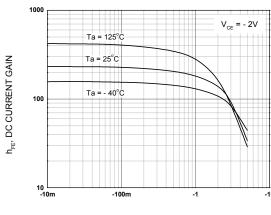


Figure 2. DC Current Gain



 $I_{\rm c}$  [A], COLLECTOR CURRENT

Figure 3. Collector-Emitter Saturation Voltage

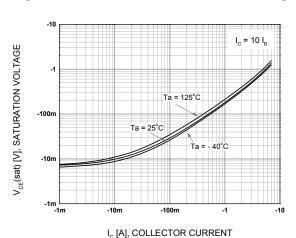
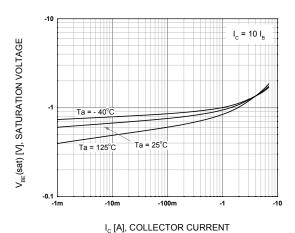


Figure 4. Base-Emitter Saturation Voltage



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Figure 5. Base-Emitter On Voltage

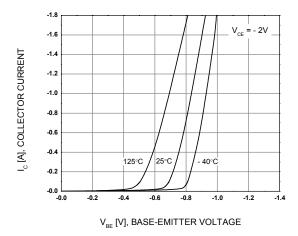
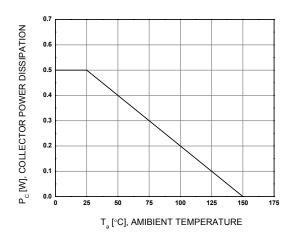


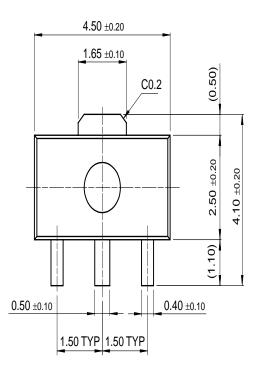
Figure 6. Power Derating

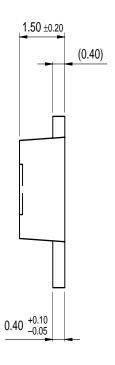


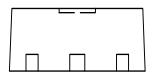
3 www.fairchildsemi.com

## **Mechanical Dimensions**

# **SOT-89**







Dimensions in Millimeters

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SuperSOT™-3

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#### **Definition of Terms**

Datasheet Identification	Product Status	Definition
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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

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